

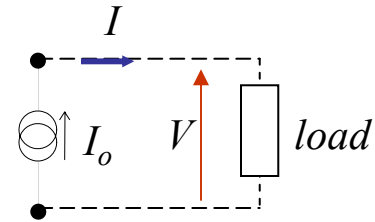
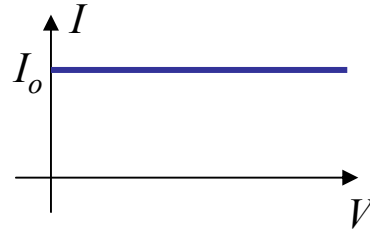
# Applications of Diodes and Transistors to Sources

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- **Current & Voltage Sources based on transistor**
  - FET-based
  - BJT-based
- **Signal Shaping**
  - Rectification
  - Clamping

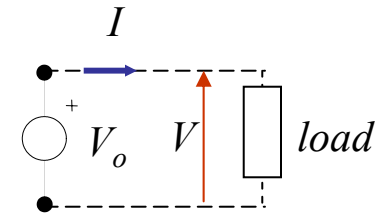
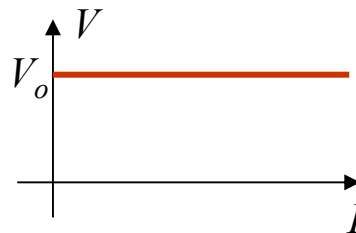
# Ideal Sources

**Ideal Current source :**



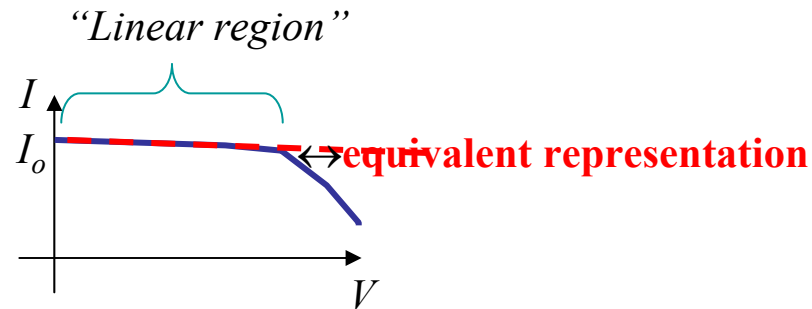
→ **Current** provided by the source is **independent** of load

**Ideal Voltage source :**



→ **Voltage** at source terminals is **independent** of load

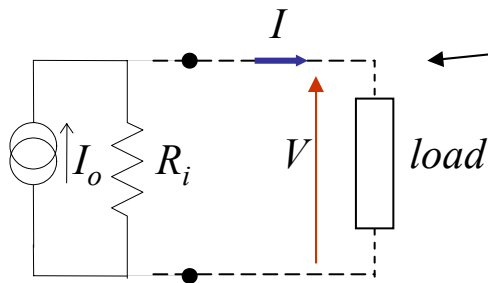
# Real Current Source



→ The linear domain is the range where the component effectively operates as a current source

## ***Equivalent schematic:***

Assumption is :  $V \in \text{linear region}$



$R_i$  = “internal resistance”  
( $G_i = 1/R_i$  = internal conductance)

$$\rightarrow I = I_o - \frac{V}{R_i}$$

$$\Rightarrow I \cong \text{const} = I_o$$

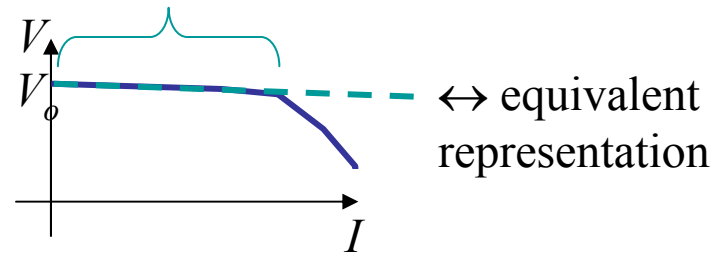
As long as  $I \gg \text{current in internal resistance}$   $\left( \frac{V}{R_i} \right)$

***This is the equivalent of Thevenin Circuit for a voltage source it is called Norton equivalent circuit.***

**current source  $\leftrightarrow R_i \gg V/I = Z_e = \text{load input impedance.}$**

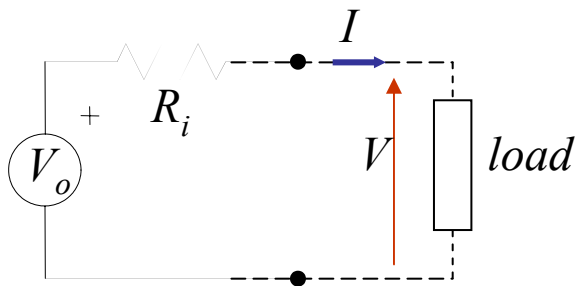
# Real Voltage Source

*Linear region*



***Equivalent schematics (Thevenin circuit):***

**assumption :**  $V \in \text{linear region}$



$$\rightarrow V = V_o - R_i I$$

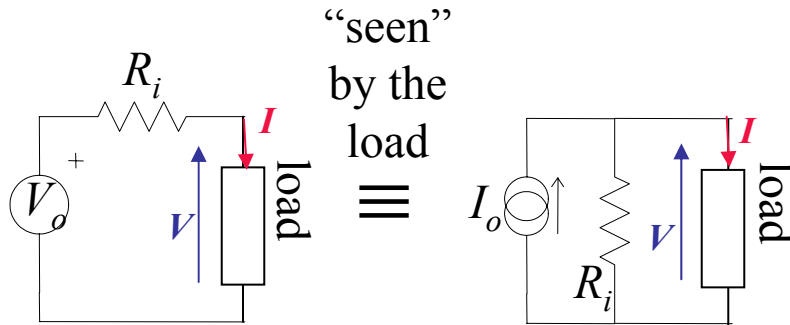
$$\Rightarrow V \cong \text{cst} = V_o$$

*As long as the voltage drop across  $R_i$  is small compared to  $V$  ( $R_i I \ll V$ )*

$$\text{Voltage source} \leftrightarrow R_i \ll Z_e$$

# Current versus Voltage Source -- Equivalence

*In fact...*



*with*

$$I_o = \frac{V_o}{R_i} = \text{“short circuit current”}$$

(load replaced by a short-circuit)

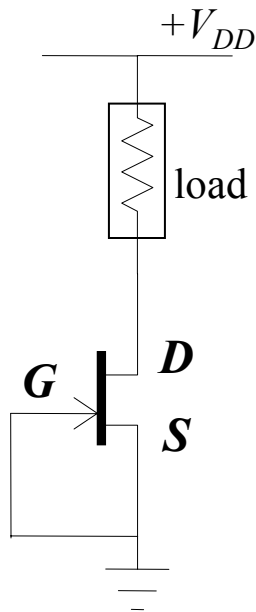
[  $V_o$  = open-circuit voltage ]


*since*


$$I = I_o - \frac{V}{R_i} = \frac{V_o}{R_i} - \frac{V}{R_i} \rightarrow V = V_o - R_i I$$

- ➡ According to the value of  $Z_e/R_i$  we have:
- Voltage source ( $Z_e \gg R_i$ )
  - Current source ( $Z_e \ll R_i$ )

# FET-based current source

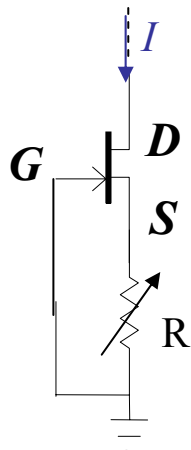


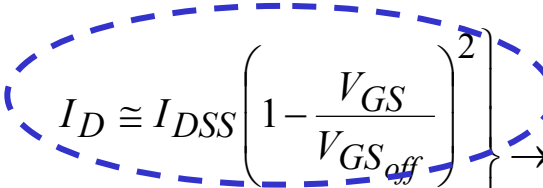
  $V_{GS} = 0 \Rightarrow I_D = I_{DSS}$ 


*Current corresponding to  $V_{GS}=0$* 


$I_{DSS}$  increases with  $V_{DS} \Leftrightarrow$  output resistance not infinite

 Current can be tunable by addition of a variable resistor





*from transistor characteristics*


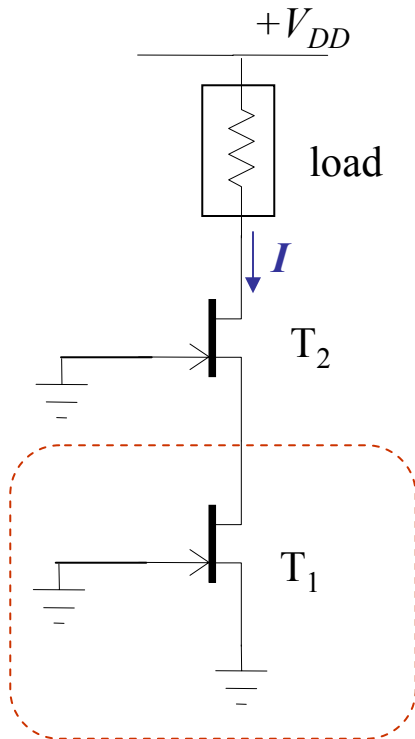
$$I_D \cong I_{DSS} \left( 1 - \frac{V_{GS}}{V_{GS_{off}}} \right)^2$$

$$I_D = -\frac{V_{GS}}{R}$$

$I_{DSS}$ : drain current with gate shorted to source

*$I_d$  and  $V_{GS}$  can be obtained by solving this system of equations*

# A better FET-based current source (greater output impedance)



Standard current source

$T_2$  and  $T_1$  operate such that  $I_{DSS}(T_2) > I_{DSS}(T_1)$

$T_1 \Rightarrow I = I_{DSS}(T_1)$

$\Rightarrow V_{GS}(T_2)$  is such that  $I_D(T_2) = I_{DSS}(T_1)$

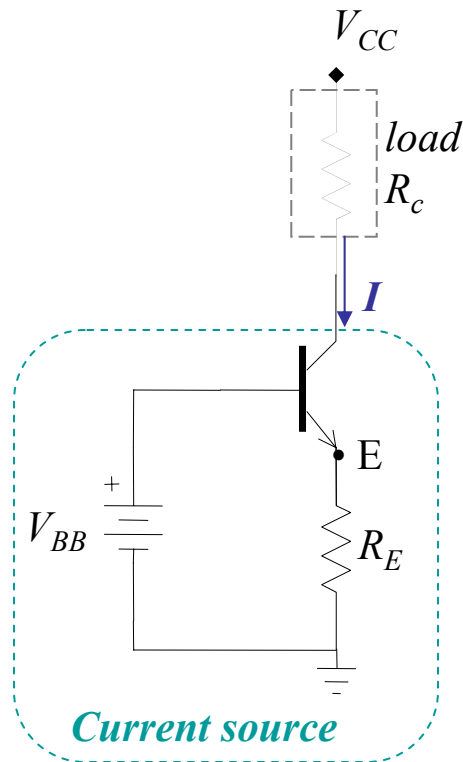
$\Rightarrow V_{DS}(T_1) = V_{GS}(T_2)$

➡ influence of load on  $V_{DS}(T_1)$  is strongly reduced

$\Rightarrow I$  vary less with respect to load variation

$\Leftrightarrow$  Output impedance is larger compare to the scheme presented in previous slide.

# BJT as current sources



$$\rightarrow I \approx \frac{V_{BB} - 0.7V}{R_E}$$

*$V_{BE} \sim 0.7V$  implies  
active mode of operation  
So  $I_E = I_C$*

**For any values of  $R_c$  ...**

as long as transistor operates in active mode

**Operating domain :** ( $V_{BB} > 0.7V$ )

$$\approx 0 < V_{CE} = V_{CC} - (R_C + R_E)I_C < V_{CC}$$

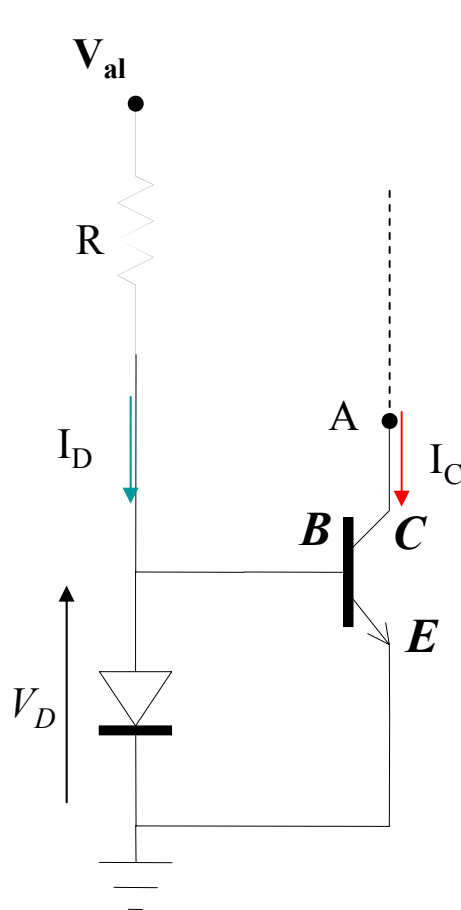
- $R_{C_{\max}} \cong \frac{V_{CC}}{I} - R_E$

for  $R_c > R_{c_{\max}} \rightarrow$  transistor in saturated regime



# BJT-based current source (current mirror)

Let's assume the characteristics  $I(V)$  of the diode is identical to the transistor BE junction



$$I_D \cong \frac{V_{al} - 0.7}{R} \quad \leftarrow V_{BE} \sim 0.7 \text{ V implies active mode of operation}$$

*So  $I_E = I_C$*

since  $V_{BE} = V_D$

→  $I_C = I_D$

*$I_C$  is the « mirror image » of  $I_D$ ...*

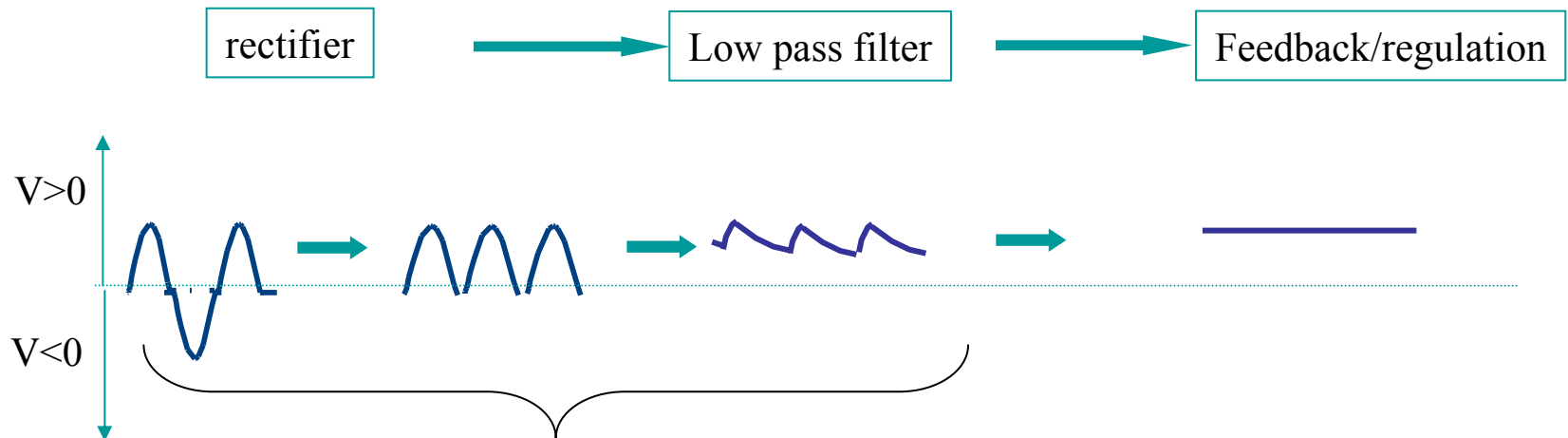
☒  $I$  does not depend on the dashed circuit  
 ⇔ seen by A, the circuit behaves as a ideal current source  
 (as long as the transistor operates in the active mode)

☒ In fact there is a small dependence of  $I_C$  upon  $V_{CE}$   
 ; this is refer to as Early effect (actually Early effect  
 is the dependence of  $\alpha_T$  on  $V_{CE}$ ).

# Diode and DC power supply

- **Aim:** Transform an AC signal in a DC signal.  
(e.g.: to supply DC voltage to an apparatus using the mains AC line)

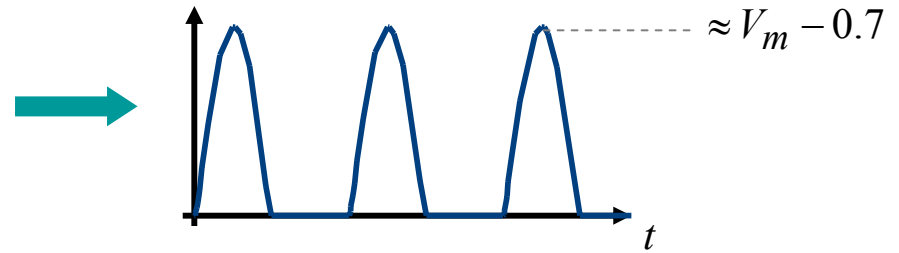
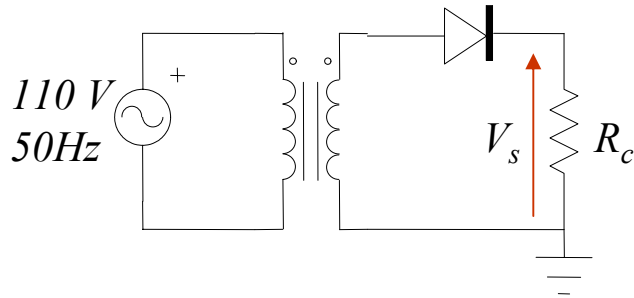
The basis steps for an AC-to-DC converter are



*What you did in Lab #8*

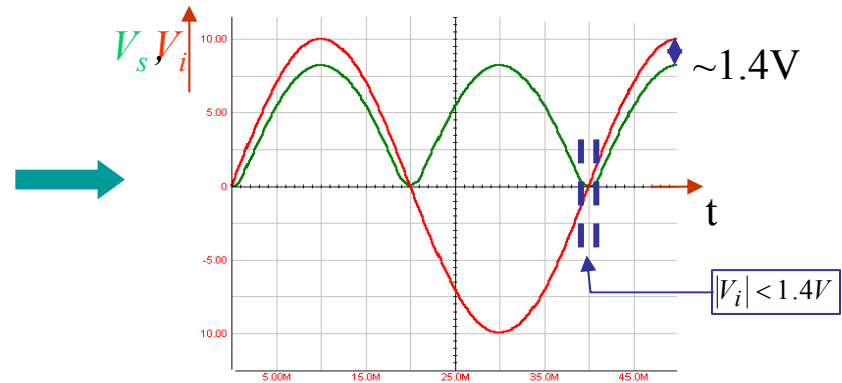
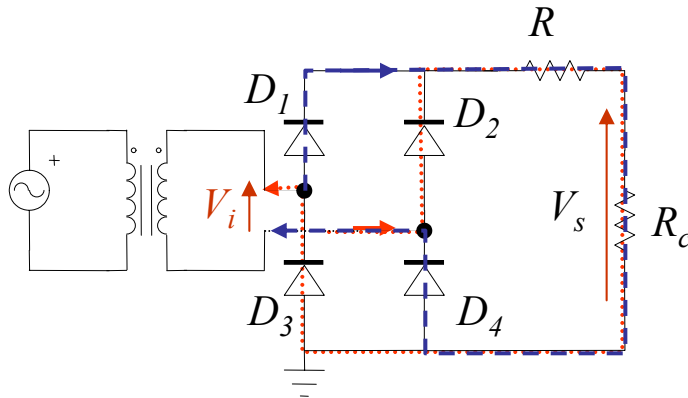
# Rectification

## Single Rectification



$R_i$  = output impedance of transformer  
 $V_m$  = secondary circuit voltage

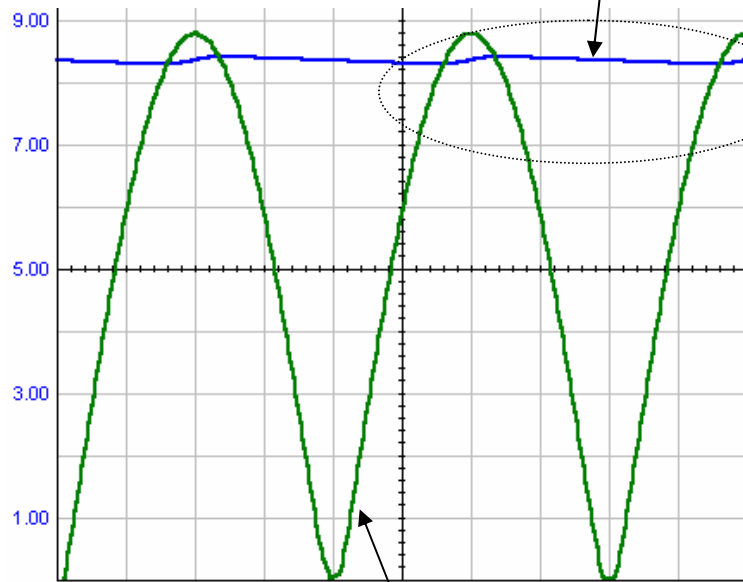
## Double Rectification



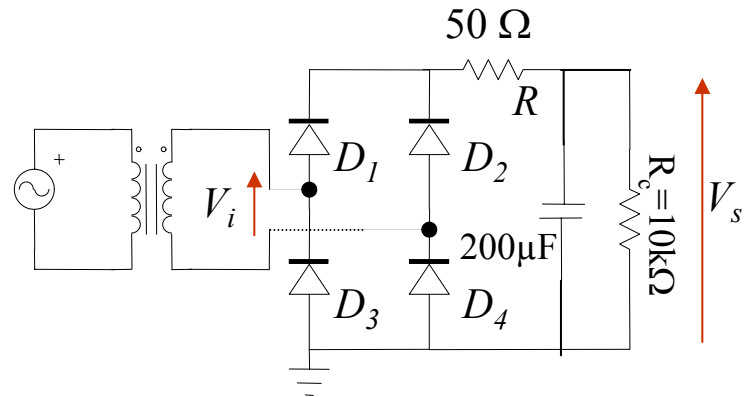
# Rectification

*With low frequency filtering*

**With capacitor**



**No capacitor**



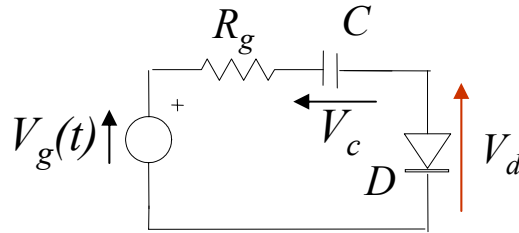
Residual ripples

Capacitor charge through  $R$   
and discharge through  $R_c$   
 $\rightarrow RC \ll R_c C$

# Clamping

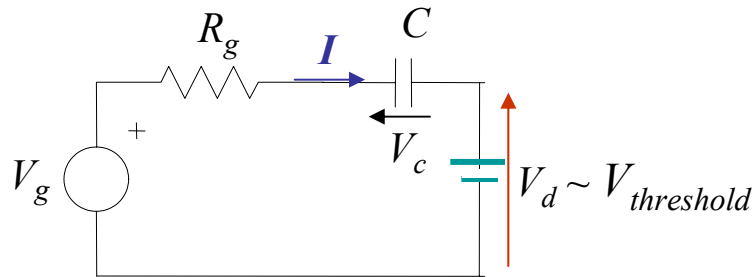
- **Fonction** : Shift the signal toward positive (or negative) voltage  
 $\leftrightarrow$  Eventually get a DC signal with a non vanishing average value

*Example :*



**Operation** : (assume a Si diode as we used in the Lab #8)

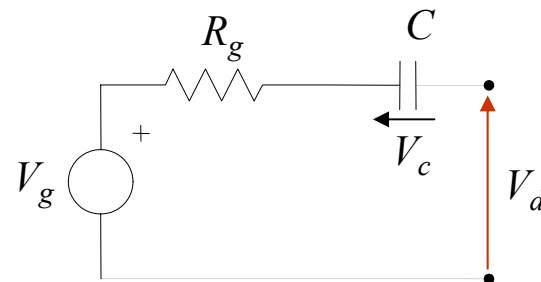
- When  $V_g - V_c > V_{threshold}$  diode forward-biased



→  $C$  charge and  $V_c$  goes toward  $V_g - V_{threshold}$

→  $V_d \sim V_{threshold}$

- With  $V_g - V_c < V_{threshold}$  diode reversed-biased



→  $V_c = \text{constant}$  (C cannot discharge!)

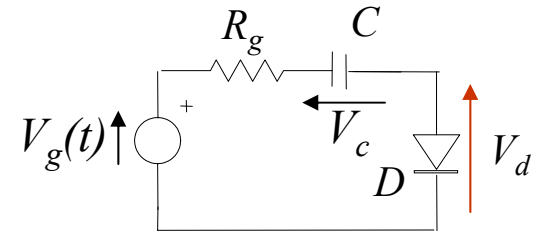
→  $V_d = V_g - V_c$   
 $\sim DC \text{ component}$

# Clamping: example

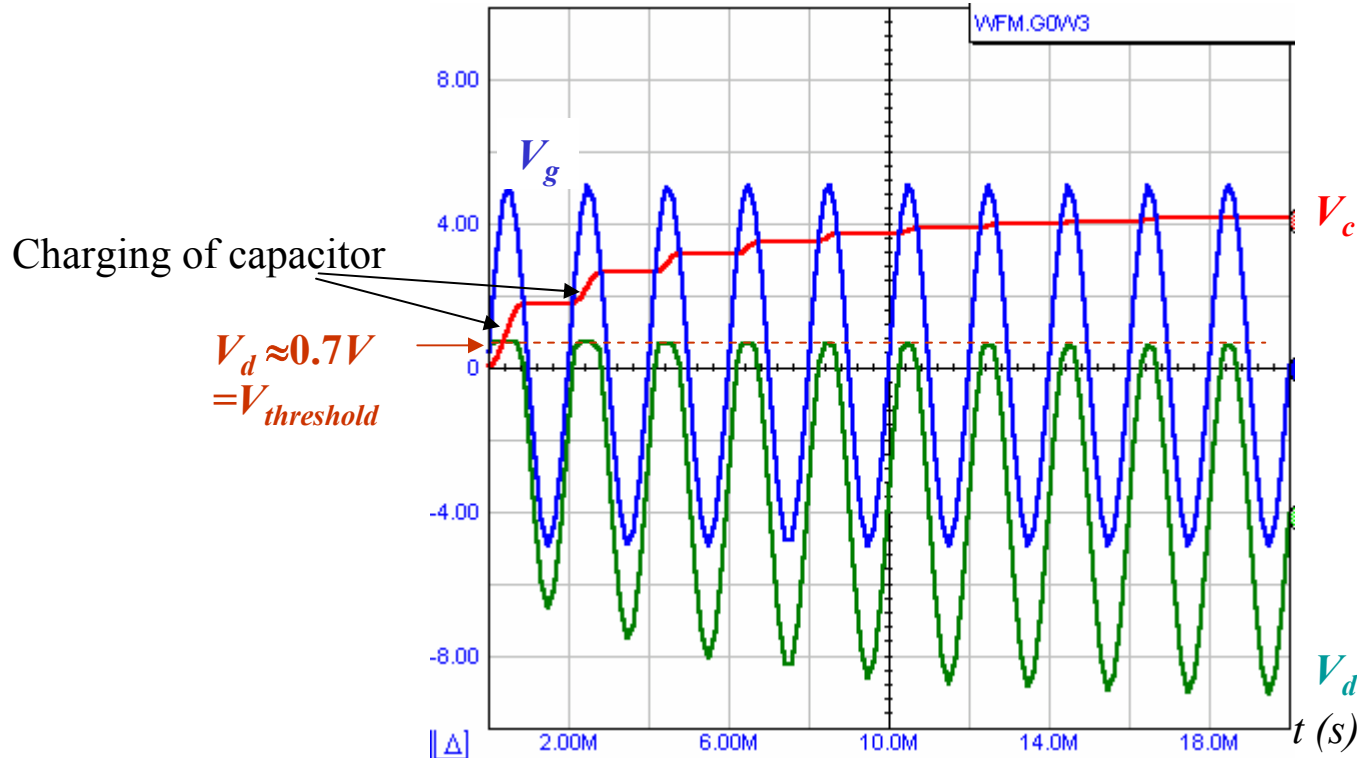
## ● Example for a sinusoidal signal

$$V_g = V_m \sin(\omega \cdot t) \text{ pour } t > 0$$

$$V_c = 0 \text{ pour } t < 0 \quad (C \text{ discharged})$$



➔ Transient where capacitor is being charged

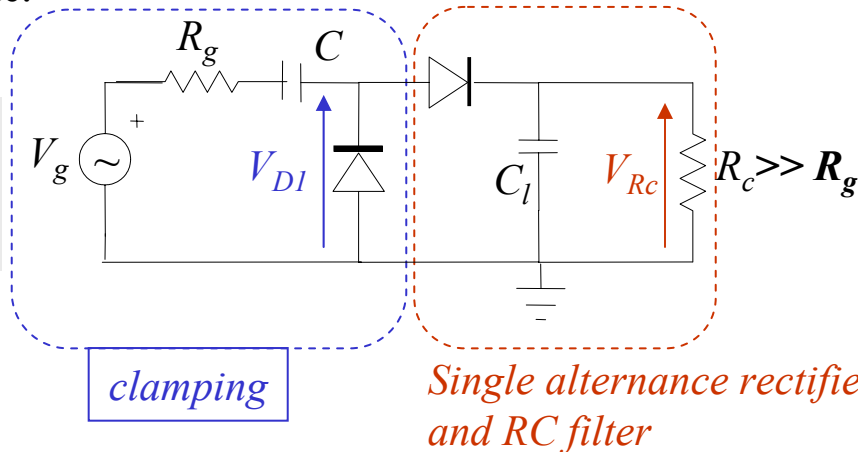


$$\begin{aligned} C &= 1\mu F \\ R_g &= 1k\Omega \\ f &= 100\text{Hz} \\ V_m &= 5\text{V} \end{aligned}$$

# Voltage multiplier

■ **Purpose :** Produce a DC voltage from an AC input signal. The DC voltage is a multiple of input signal amplitude.

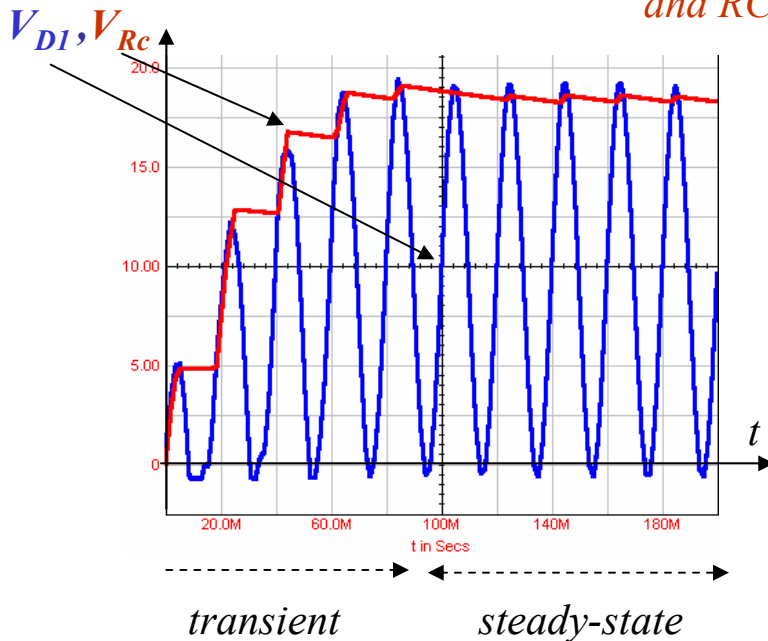
**Example :**  
**Voltage Doubler**



$$V_g = V_m \sin(2\pi f \cdot t) \text{ for } t > 0$$

$$V_m = 10\text{V}, f = 50\text{Hz}, C = 10\mu\text{F}$$

$$R_c = 100\text{k}\Omega.$$



\* In steady state input current is small so high input impedance.

$$\rightarrow V_{R_c} \cong 2 \cdot V_m$$

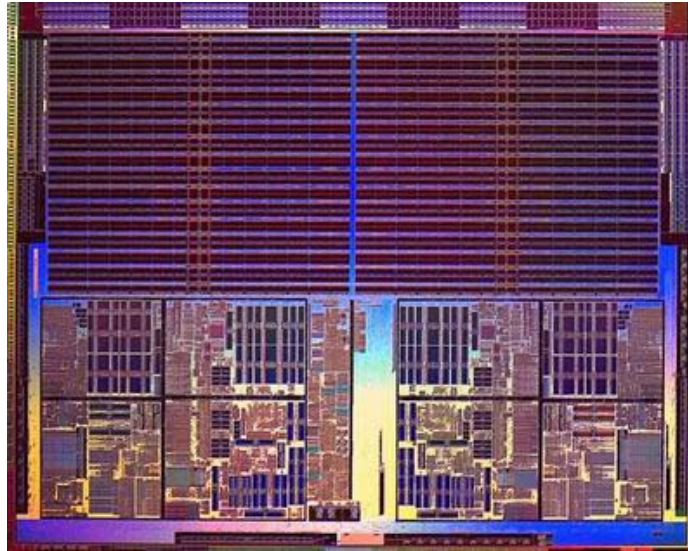
\* This is not a good voltage source since output current (in  $R_c$ ) must remain small ( $\sim$  high internal impedance)

# Summary

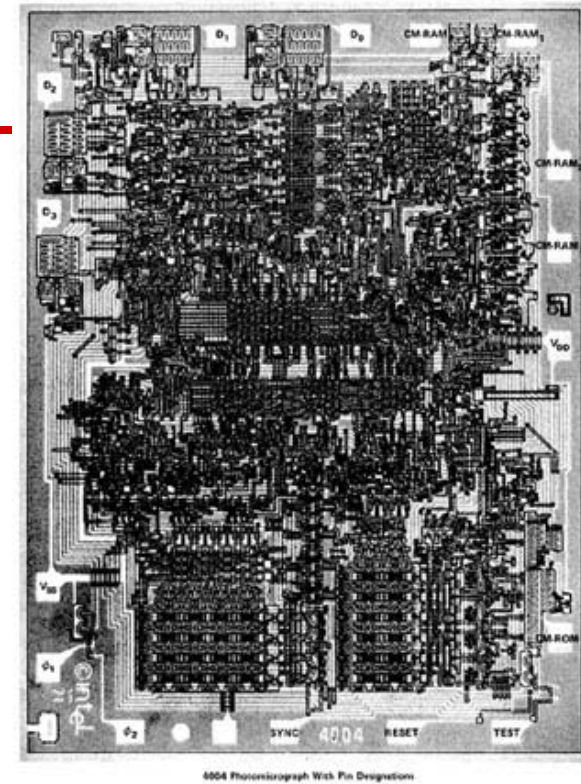
- Transistor and diode find many application in power supply (either as current or voltage source)
- Diode are used in scheme aimed at generating DC signal from an input AC signal
- There is another class of applications of transistor: amplifier



*1947: The 1<sup>st</sup> transistor*



*Today: ATHLON 64 dual core:  
233000000 transistors*



*1971: intel processor 4004:  
2250 transistors*